## Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.455 \text{ V}$  at  $I_F = 5 \text{ A}$ 

#### **Features**

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

#### **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

#### **Mechanical Characteristics**

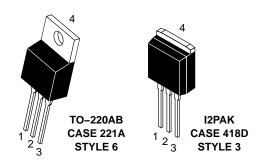
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

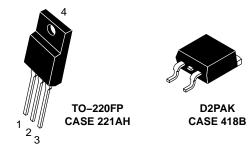


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# PIN CONNECTIONS 2,





#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

#### **MAXIMUM RATINGS**

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
Average Rectified Forward Current (Rated V <sub>R</sub> , T <sub>C</sub> = 115°C)	Per device Per diode	I <sub>F(AV)</sub>	30 15	А
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 110°C)	Per device Per diode	I <sub>FRM</sub>	60 30	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	160	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T <sub>stg</sub>	-40 to +150	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/µs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Rating	Symbol	NTST30100CTG, NTSB30100CT-1G	NTSB30100CTG	NTSJ30100CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$egin{array}{c} {\sf R}_{ heta {\sf JC}} \ {\sf R}_{ heta {\sf JA}} \end{array}$	2.5 70	1.14 46.6	4.09 105	°C/W

#### **ELECTRICAL CHARACTERISTICS** (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) (I <sub>F</sub> = 5 A, T <sub>I</sub> = 25°C)	VF	0.516		V
$(I_F = 7.5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.576		
$(I_F = 15 \text{ A}, T_J = 25^{\circ}\text{C})$		0.734	0.85	
(I <sub>F</sub> = 5 A, T <sub>J</sub> = 125°C) (I <sub>F</sub> = 7.5 A, T <sub>J</sub> = 125°C)		0.455 0.522		
(I <sub>F</sub> = 15 A, T <sub>J</sub> = 125°C)		0.627	0.68	
Maximum Instantaneous Reverse Current (Note 1) $(V_R = 70 \text{ V}, T_{\perp} = 25^{\circ}\text{C})$	I <sub>R</sub>	7.2		
$(V_R = 70 \text{ V}, T_J = 23 \text{ G})$ $(V_R = 70 \text{ V}, T_J = 125 ^{\circ}\text{C})$		8.0		μA mA
(Rated dc Voltage, T <sub>J</sub> = 25°C)		65	500	μА
(Rated dc Voltage, T <sub>J</sub> = 125°C)		20	35	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width =  $300 \,\mu s$ , Duty Cycle  $\leq 2.0\%$ 

#### **TYPICAL CHARACTERISITICS**

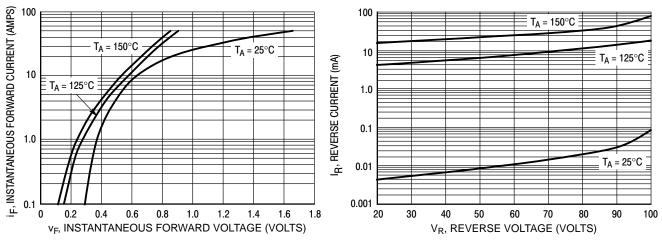


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

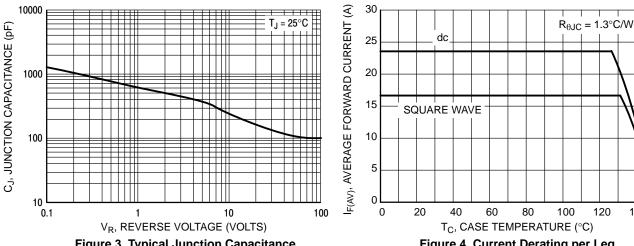


Figure 3. Typical Junction Capacitance

Figure 4. Current Derating per Leg

120

140

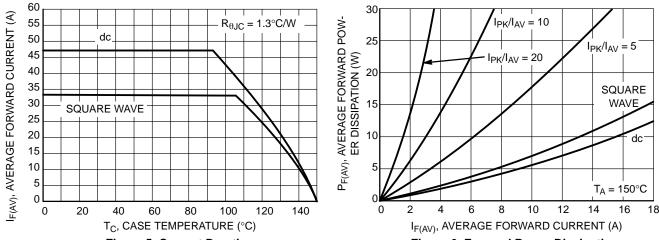


Figure 5. Current Derating

Figure 6. Forward Power Dissipation

#### **TYPICAL CHARACTERISITICS**

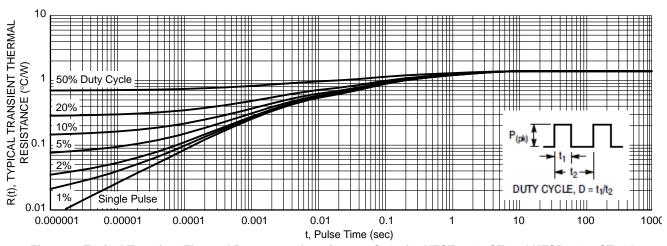


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30100CT and NTSB30100CT-1G

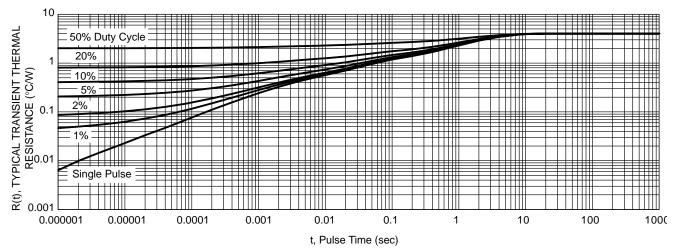


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30100CTG

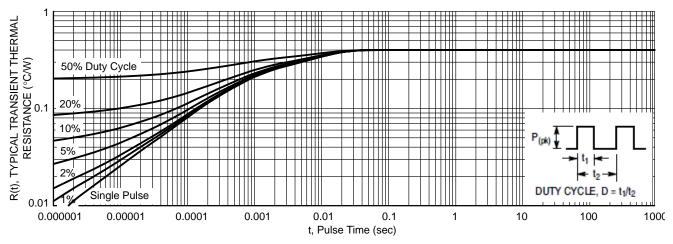
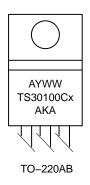


Figure 9. Typical Transient Thermal Response, Junction-to-Case for NTSB30100CTG

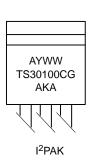
#### **ORDERING INFORMATION**

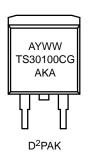
Device	Package	Shipping
NTST30100CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSB30100CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSJ30100CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30100CTG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB30100CTT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

#### **MARKING DIAGRAMS**







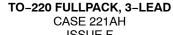


A = Assembly Location

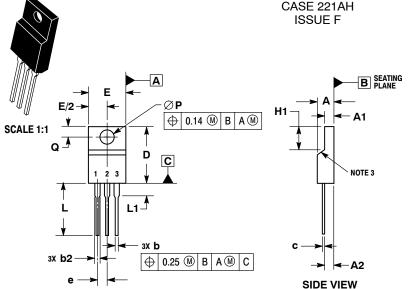
Y = Year
WW = Work Week
AKA = Polarity Designator

x = G or H

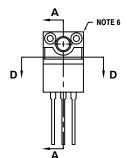
G = Pb-Free Package H = Halide-Free Package

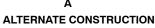


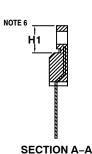
**DATE 30 SEP 2014** 











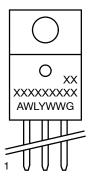
STYLE 1: STYLE 2: PIN 1. MAIN TERMINAL 1 PIN 1. CATHODE MAIN TERMINAL 2 ANODE 2. 2 GATE GATE

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
  3. CONTOUR UNCONTROLLED IN THIS AREA.
- CONTOUR ONCOUNTIOLLED IN THIS AREA.
   DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
   DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
   LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.30	4.70		
A1	2.50	2.90		
A2	2.50	2.90		
b	0.54	0.84		
b2	1.10	1.40		
С	0.49	0.79		
D	14.70	15.30		
E	9.70	10.30		
е	2.54	BSC		
H1	6.60	7.10		
L	12.50	14.73		
L1		2.80		
P	3.00	3.40		
Q	2.80	3.20		

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON52577E	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-220 FULLPACK, 3-LEAD		PAGE 1 OF 1

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## **MECHANICAL CASE OUTLINE**

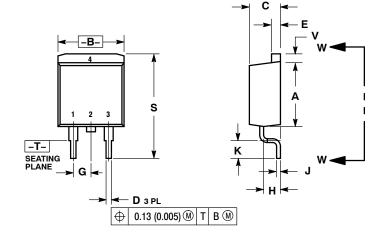




D<sup>2</sup>PAK 3 CASE 418B-04 **ISSUE L** 

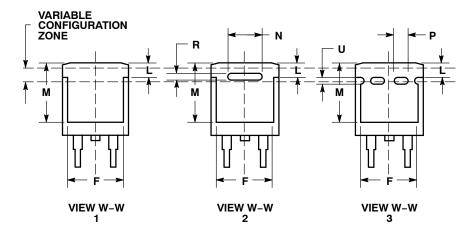
**DATE 17 FEB 2015** 

#### SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES MILLIMET		IETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54 BSC	
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079	REF	2.00 REF	
R	0.039 REF		0.99	REF
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:

PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6:

PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

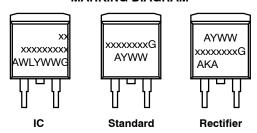
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**DATE 17 FEB 2015** 

## GENERIC MARKING DIAGRAM\*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

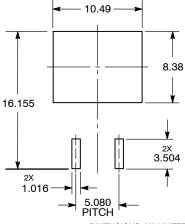
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

#### **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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